

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD002P** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	250 mA
V_{CC}	37 V
P_{DISS}	10 W @ T _C ≤ 100 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	10 °C/W

PACKAGE STYLE .280 4L PILL (A)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

ORDER CODE: ASI10553

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1 mA	45			V
BV_{CER}	I _C = 5 mA R _{BE} = 10 Ω	45			V
BV_{EBO}	I _E = 1 mA	3.5			V
I_{CES}	V _{CE} = 35 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 A	30		300	---
P_G	V _{CC} = 35 V P _{OUT} = 2.0 W f = 1025 – 1150	9.0			dB
η_c	MHZ	35			%